

L15 ANSWER 11 OF 12 HCAPLUS COPYRIGHT 2003 ACS on STN
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 TI Deposition of Ta₂O₅ and (TiO₂)-(Ta₂O₅) films from Ta(OEt)₄(DMAE) and
 Ti(OEt)₂(DMAE)2, by IMOCVD
 AU Jimenez, C.; Paillous, M.; Madar, R.; Senateur, J. P.; Jones, A. C.
 CS LMGP-INPG, URA 1109, ENSPG, Saint-Martin-d'Heres, 38402, Fr.
 SO Journal de Physique IV: Proceedings (1999), 9(Pr8, Proceedings of the
 Twelfth European Conference on Chemical Vapour Deposition, 1999, Vol. 2),
 569-573
 CODEN: JPICEI; ISSN: 1155-4339
 PB EDP Sciences
 DT Journal
 LA English
 CC 75-1 (Crystallography and Liquid Crystals)
 AB Ta₂O₅ and (TiO₂)-(Ta₂O₅) films were deposited on Si at low temp. by
 injection metalorg. CVD (IMOCVD) using tetraethoxy(dimethylaminoethoxy)tan
 talum, Ta(OEt)₄(DMAE) and diethoxybis(dimethylaminoethoxy)titanium,
 Ti(OEt)₂(DMAE)2 as precursors. O was used in some cases as oxidizing
 agent; nevertheless, films were also obtained without O. The influence of
 deposition conditions on the deposition process and structural properties
 of the films was studied by FTIR, electron-probe microanal. and XRD.
 IT 172901-22-3
 RL: PEP (Physical, engineering or chemical process); PROC (Process)
 (injection metalorg. of Ta₂O₅ films using precursor)
 RN 172901-22-3 HCAPLUS
 CN Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-,
 (OC-6-23)- (9CI) (CA INDEX NAME)

